

forming a third insulating film on said second insulating film, said third insulating film being made of a material different from that of the second insulating film and having a thickness larger than that of the second insulating film;

forming a groove in a region of said third insulating film, in which a wiring is to be formed, said groove having a bottom to which said second insulating film is exposed;

removing a part of that portion of the second insulating film which is exposed to the groove, and a part of the first insulating film under the portion of the second insulating film, using the same etching mask, and thus forming a contact hole reaching to the semiconductor substrate; and

burying the groove and the contact hole with a metal to form a metal wiring in said groove and a metal contact in said contact hole.

IN THE TITLE

Please change the title to read:

PROCESS FOR FABRICATING A METAL WIRING AND METAL CONTACT IN A SEMICONDUCTOR DEVICE

REMARKS

Favorable reconsideration of this application is respectfully requested.

As requested by the examiner, a new title has been added and is believed to be clearly indicative of the subject matter to which the claims are directed.

Claims 29-40 are present in this application. Claims 29, 31 and 40 stand rejected under 35 U.S.C. §102(b) as anticipated by U.S. 4,789,648 (Chow et al). Under 35 U.S.C. §103(a), claim 30 stands rejected over Chow et al in view of U.S. 4,832,789 (Cochran et al),